

# SI2328DS-T1-GE3

## SI2328DS-T1-GE3 Information

www.letspuer.com	 SI2328DS-T1-GE3 Vishay Siliconix Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single MOSFET N-CH 100V 1.15A SOT-23 TO-236-3, SC-59, SOT-23-3 For the pricing/inventory/lead time, please contact	
For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

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# SI2328DS-T1-GE3 Specifications

Manufacturer Part NumberSt252bDs-11-GESManufacturerVishay SiliconixCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-236-3, SC-59, SOT-23-3SeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1.15A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ VgsSnC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTo-236-3, SC-59, SOT-23-3SeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1.15A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds20VFET Feature-Power Dissipation (Max)250 mOhm @ 1.5A, 10VOperating Temperature-55° < 150°C (TJ)	Manufacturer Part Number	SI2328DS-T1-GE3
PackageTransistors - FETs, MOSFETs - SinglePackageTO-236-3, SC-59, SOT-23-3SeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1.15A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vds5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Manufacturer	Vishay Siliconix
PackageTO-236-3, SC-59, SOT-23-3SeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1.15A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)250 mOhm @ 1.5A, 10VQerating Temperature-55°C ~ 150°C (TJ)Operating TemperatureSurface MountMounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Category	Discrete Semiconductor Products
Series TrenchFET?   FET Type N-Channel   Technology MOSFET (Metal Oxide)   Drain to Source Voltage (Vdss) 100V   Current - Continuous Drain (Id) @ 25°C 1.15A (Ta)   Drive Voltage (Max Rds On, Min Rds On) 10V   Vgs(th) (Max) @ Id 4V @ 250μA   Gate Charge (Qg) (Max) @ Vgs 5nC @ 10V   Input Capacitance (Ciss) (Max) @ Vds -   Ygs (Max) ±20V   FET Feature -   Power Dissipation (Max) 30mW (Ta)   Qf on (Max) @ Id, Vgs 250 mOhm @ 1.5A, 10V   Operating Temperature -   Power Dissipation (Max) Stor nohm @ 1.5A, 10V   Operating Temperature -   Mounting Type Surface Mount   Supplier Device Package SOT-233 (TO-236)   Package / Case TO-236-3, SC-59, SOT-23-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1.15A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vds5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Ygs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)	Package	TO-236-3, SC-59, SOT-23-3
TechnologyMOSFET (Metal Oxide)TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C1.15A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Series	TrenchFET?
Drain to Source Voltage (Vdss) 100V   Current - Continuous Drain (Id) @ 25°C 1.15A (Ta)   Drive Voltage (Max Rds On, Min Rds On) 10V   Vgs(th) (Max) @ Id 4V @ 250µA   Gate Charge (Qg) (Max) @ Vgs 5nC @ 10V   Input Capacitance (Ciss) (Max) @ Vds -   Vgs (Max) ±20V   FET Feature -   Power Dissipation (Max) 730mW (Ta)   Rds On (Max) @ Id, Vgs 250 mOhm @ 1.5A, 10V   Operating Temperature -55°C ~ 150°C (TJ)   Mounting Type Surface Mount   Supplier Device Package SOT-23-3 (TO-236)   Package / Case TO-236-3, SC-59, SOT-23-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C 1.15A (Ta)   Drive Voltage (Max Rds On, Min Rds On) 10V   Vgs(th) (Max) @ Id 4V @ 250µA   Gate Charge (Qg) (Max) @ Vgs 5nC @ 10V   Input Capacitance (Ciss) (Max) @ Vds -   Vgs (Max) ±20V   FET Feature -   Power Dissipation (Max) 730mW (Ta)   Rds On (Max) @ Id, Vgs 250 mOhm @ 1.5A, 10V   Operating Temperature -55°C ~ 150°C (TJ)   Mounting Type Surface Mount   Supplier Device Package SOT-23.3 (TO-236)   Package / Case TO-236-3, SC-59, SOT-23.3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id4V @ 250µAGate Charge (Qg) (Max) @ Vgs5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Current - Continuous Drain (Id) @ 25°C	1.15A (Ta)
Gate Charge (Qg) (Max) @ Vgs5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Vgs(th) (Max) @ Id	4V @ 250µA
Ygs (Max)±20VFET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	5nC @ 10V
FET Feature-Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max)730mW (Ta)Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs250 mOhm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	730mW (Ta)
Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	250 mOhm @ 1.5A, 10V
Supplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
-	Supplier Device Package	SOT-23-3 (TO-236)
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

#### SI2328DS-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. \* If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

# SERVICE BUARANTEE

#### **Service Guarantees**

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

### SI2328DS-T1-GE3 Payment Methods



# SI2328DS-T1-GE3 Shipping Methods



If you have any question about SI2328DS-T1-GE3, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com